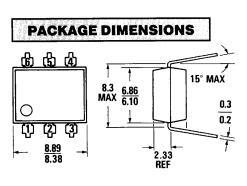
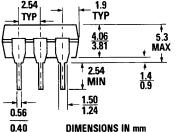


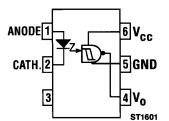
H11L1 H11L2 H11L3





DIMENSIONS IN mm PACKAGE CODE K





Equivalent Circuit

DESCRIPTION

The H11L series has a medium-to-high speed integrated circuit detector optically coupled to a gallium-arsenide infrared emitting diode. The output incorporates a Schmitt trigger, which provides hysteresis for noise immunity and pulse shaping. The detector circuit is optimized for simplicity of operation and utilizes an open collector output for maximum application flexibility.

FEATURES

- High data rate, 1 MHz typical (NRZ)
- Free from latch up and oscillation throughout voltage and temperature ranges.
- Microprocessor compatible drive
- Logic compatible output sinks 16 mA at 0.4 V
- maximum
- Guaranteed on/off threshold hysteresis
- High common mode rejection ratio
- Fast switching: t_r, t_f=100 ns typical
- Wide supply voltage capability, compatible with all popular logic systems
- Underwriters Laboratory (UL) recognized file #E90700

APPLICATIONS

- Logic to logic isolator
- Programmable current level sensor
- Line receiver—eliminate noise and transient problems
- A.C. to TTL conversion—square wave shaping
- Digital programming of power supplies

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Interfaces computers with peripherals

ABSOLUTE MAXIMUM RATINGS

Storage temperature55°C to 150°C
Operating temperature55°C to 100°C
Lead solder temperature 260°C for 10 sec
INPUT DIODE
Power dissipation (25°C ambient) 100 mW
Derate linearly (above 25°C ambient) 1.33 mW/°C
Continuous forward current 60 mA
Peak forward current (1 µs pulse, 300pps) 3 A

Reverse voltage 6 V

DETECTOR Power dissipation

Power dissipation (at 25°C ambient)	150 mW
Derate linearly (above 25°C ambient)	2 mW/°C
V_{45} allowed range	0 to 16 V
V_{65} allowed range	0 to 16 V
l₄ output current	50 mA

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SEMICONDUCTOR

ELECTRICAL CHARACTERISTICS (T_A= 0-70°C Unless Otherwise Specified)

INDIVIDUAL COMPONENT CHARACTERISTICS								
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS		
INPUT DIODE								
Forward voltage	V _F		1.1	1.5	V	l _F =10 mA		
	V _F	0.75	0.95		V	l _⊧ =0.3 mA		
Reverse current	I _R			10	μA	V _R =3 V		
Capacitance	C			100	pF	V=0, f=1 MHz		
OUTPUT DETECTOR Operating voltage range	V _{cc}	3		15	V			
Supply current	I _{6(off)}		1.0	5.0	mA	I _F =0, V _{CC} =5 V		
Output current, high	I _{он}			100	μA	$I_{\rm F}$ =0, $V_{\rm cc}$ = $V_{\rm o}$ =15 V		

TRANSFER CHARACTERISTICS								
CHARACTERISTIC	:	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS	
Supply current		$I_{6(on)}$		1.6	5	mA	$I_{\rm F}$ =10 mA, $V_{\rm cc}$ =5 V	
Output voltage, low		Vol		0.2	0.4	V	$\begin{array}{l} R_{L} = 270 \ \Omega, \ V_{CC} = 5 \ V, \\ I_{F} = I_{F(on)} \ max. \end{array}$	
Turn-on threshold current	(H11L1)	I _{F(on)}		1.0	1.6	mA	$R_L=270 \Omega, V_{CC}=5 V$	
	(H11L2)	I _{F(on)}		6.0	10.0	mA	R _L =270 Ω, V _{cc} =5 V	
	(H11L3)	I _{F(on)}		3.0	5.0	mA	R _L =270 Ω, V _{cc} =5 V	
Turn-off threshold current		_{F(off)}	0.3	1.0		mA	R _L =270 Ω, V _{cc} =5 V	
Hysteresis ratio		I _{F(off)} /I _{F(on)}	0.50	0.75	0.90		R _L =270 Ω, V _{cc} =5 V	

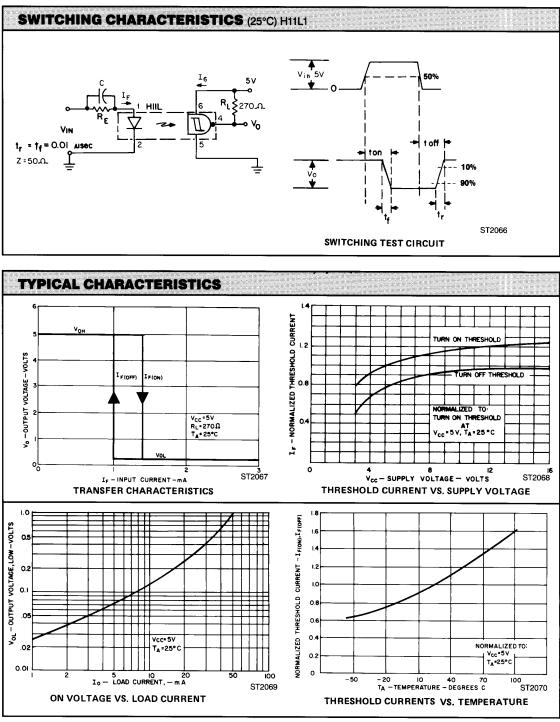


PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
SWITCHING SPEED Turn-on time	t _{on}		1.0		μS	C=0, R _E =1.2 k Ω
	t _{on}		0.65		μs	C=270 pF, R _E =1.2 kΩ f≤100 KHz, tp≥1 μs
Fall time	t,		0.1		μs	C=0,R _E =1.2 kΩ
	t,		0.05		μs	C=270 pF, R _e =1.2 kΩ f≤100 KHz, tp≥1 μs
Turn-off time	t _{OFF}		2.0		μs	$C=0,R_{E}=1.2 k\Omega$
	t _{off}		1.20		μs	C=270 pF, R _ε =1.2 kΩ f≤100 KHz, tp≥1 μs
Rise time	t,		0.1		μs	C=0,R _E =1.2 kΩ
	t,		0.07		μs	C=270 pF, R _ε =1.2 kΩ f≤100 KHz, tp≥1 μs
Data rate			1.0*		MHz	

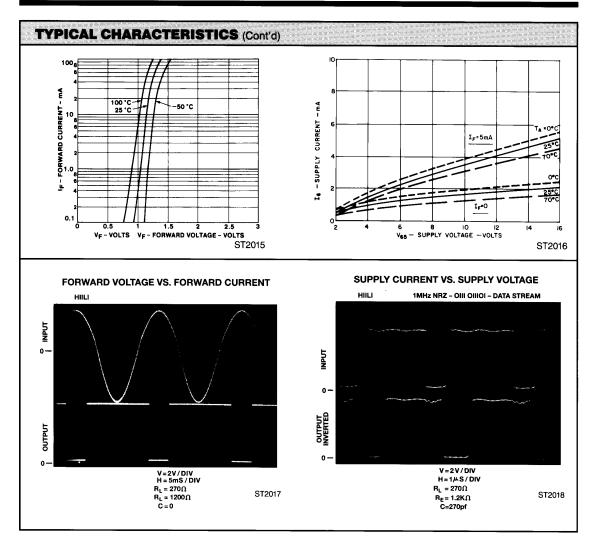
ISOLATION CHA	RACTERIST	ICS				
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Surge isolation voltage	V _{ISO}	7500			V _{PEAK}	1 Minute
Surge isolation voltage	V _{iso}	5300			V _{RMS}	1 Minute

*Maximum data rate will vary depending on the bias conditions and is usually highest when R_{ϵ} and C are matched to $I_{r(on)}$ and V_{cc} is between 3 and 15 V. With this optimized bias, most units will operate over 1.5 MHz (NRZ).

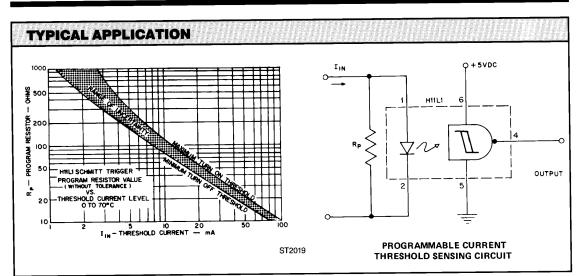














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